

## 54ABT245 Octal Bidirectional Transceiver with TRI-STATE® Outputs

### General Description

The 54ABT245 contains eight non-inverting bidirectional buffers with TRI-STATE outputs and is intended for bus-oriented applications. Current sinking capability is 48 mA on both the A and B ports. The Transmit/Receive (T/R) input determines the direction of data flow through the bidirectional transceiver. Transmit (active HIGH) enables data from A ports to B ports; Receive (active LOW) enables data from B ports to A ports. The Output Enable input, when HIGH, disables both A and B ports by placing them in a High Z condition.

### Features

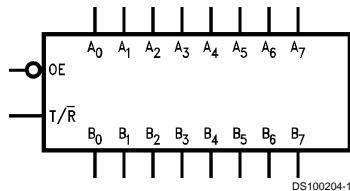
- Bidirectional non-inverting buffers
- A and B output sink capability of 48 mA, source capability of 24 mA

- Guaranteed output skew
- Guaranteed multiple output switching specifications
- Output switching specified for both 50 pF and 250 pF loads
- Guaranteed simultaneous switching, noise level and dynamic threshold performance
- Guaranteed latchup protection
- High impedance glitch-free bus loading during entire power up and power down cycle
- Non-destructive hot insertion capability
- Disable time is less than enable time to avoid bus contention
- Standard Microcircuit Drawing (SMD) 5962-9214801

### Ordering Code:

Military	Package Number	Package Description
54ABT245J-QML	J20A	20-Lead Ceramic Dual-In-Line
54ABT245W-QML	W20A	20-Lead Cerpak
54ABT245E-QML	E20A	20-Lead Ceramic Leadless Chip Carrier, Type C

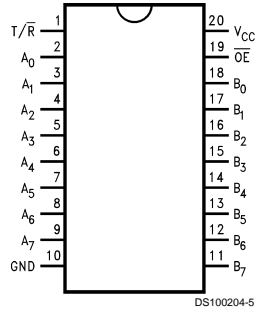
### Logic Symbol



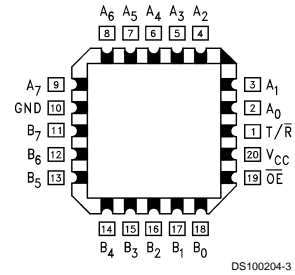
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## Connection Diagrams

Pin Assignment for DIP and Flatpak.



Pin Assignment for LCC



## Pin Descriptions

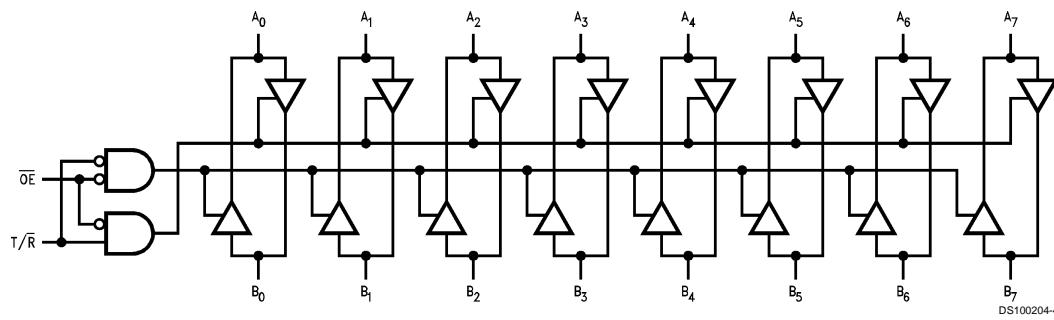
Pin Names	Description
$\overline{OE}$	Output Enable Input (Active LOW)
$T/\overline{R}$	Transmit/Receive Input
$A_0$ - $A_7$	Side A Inputs or TRI-STATE Outputs
$B_0$ - $B_7$	Side B Inputs or TRI-STATE Outputs

## Truth Table

Inputs		Output
$\overline{OE}$	$T/\overline{R}$	
L	L	Bus B Data to Bus A
L	H	Bus A Data to Bus B
H	X	High Z State

H = HIGH Voltage Level  
L = LOW Voltage Level  
X = Immaterial

## Logic Diagram



## Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature	-65°C to +150°C
Ambient Temperature under Bias	-55°C to +125°C
Junction Temperature under Bias	
Ceramic	-55°C to +175°C
V <sub>CC</sub> Pin Potential to Ground Pin	-0.5V to +7.0V
Input Voltage (Note 2)	-0.5V to +7.0V
Input Current (Note 2)	-30 mA to +5.0 mA
Voltage Applied to Any Output in the Disabled or Power-off State	-0.5V to 5.5V
in the HIGH State	-0.5V to V <sub>CC</sub>
Current Applied to Output	

in LOW State (Max)	twice the rated I <sub>OL</sub> (mA)
DC Latchup Source Current	-500 mA
Over Voltage Latchup (I/O)	10V

## Recommended Operating Conditions

Free Air Ambient Temperature	
Military	-55°C to +125°C
Supply Voltage	
Military	+4.5V to +5.5V
Minimum Input Edge Rate	(ΔV/Δt)
Data Input	50 mV/ns
Enable Input	20 mV/ns

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

## DC Electrical Characteristics

Symbol	Parameter		ABT245			Units	V <sub>CC</sub>	Conditions
			Min	Typ	Max			
V <sub>IH</sub>	Input HIGH Voltage		2.0			V		Recognized HIGH Signal
V <sub>IL</sub>	Input LOW Voltage					V		Recognized LOW Signal
V <sub>CD</sub>	Input Clamp Diode Voltage					V	Min	I <sub>IN</sub> = -18 mA ( $\overline{OE}$ , T/ $\overline{R}$ )
V <sub>OH</sub>	Output HIGH Voltage	54ABT	2.5		V	Min	I <sub>OH</sub> = -3 mA (A <sub>n</sub> , B <sub>n</sub> )	
		54ABT	2.0		V	Min	I <sub>OH</sub> = -24 mA (A <sub>n</sub> , B <sub>n</sub> )	
V <sub>OL</sub>	Output LOW Voltage	54ABT	0.55		V	Min	I <sub>OL</sub> = 48 mA (A <sub>n</sub> , B <sub>n</sub> )	
I <sub>IH</sub>	Input HIGH Current		5		μA	Max	V <sub>IN</sub> = 2.7V ( $\overline{OE}$ , T/ $\overline{R}$ ) (Note 3) V <sub>IN</sub> = V <sub>CC</sub> ( $\overline{OE}$ , T/ $\overline{R}$ )	
I <sub>BVI</sub>	Input HIGH Current Breakdown Test		7		μA	Max	V <sub>IN</sub> = 7.0V ( $\overline{OE}$ , T/ $\overline{R}$ )	
I <sub>BVIT</sub>	Input HIGH Current Breakdown Test (I/O)		100		μA	Max	V <sub>IN</sub> = 5.5V (A <sub>n</sub> , B <sub>n</sub> )	
I <sub>IL</sub>	Input LOW Current		-5		μA	Max	V <sub>IN</sub> = 0.5V ( $\overline{OE}$ , T/ $\overline{R}$ ) (Note 3) V <sub>IN</sub> = 0.0V ( $\overline{OE}$ , T/ $\overline{R}$ )	
V <sub>ID</sub>	Input Leakage Test		4.75		V	0.0	I <sub>ID</sub> = 1.9 μA ( $\overline{OE}$ , T/ $\overline{R}$ ) All Other Pins Grounded	
I <sub>IH</sub> + I <sub>OZH</sub>	Output Leakage Current		50		μA	0 - 5.5V	V <sub>OUT</sub> = 2.7V (A <sub>n</sub> , B <sub>n</sub> ); $\overline{OE}$ = 2.0V	
I <sub>IL</sub> + I <sub>OZL</sub>	Output Leakage Current		-50		μA	0 - 5.5V	V <sub>OUT</sub> = 0.5V (A <sub>n</sub> , B <sub>n</sub> ); $\overline{OE}$ = 2.0V	
I <sub>OS</sub>	Output Short-Circuit Current		-100		-275	mA	Max	V <sub>OUT</sub> = 0.0V (A <sub>n</sub> , B <sub>n</sub> )
I <sub>CEX</sub>	Output High Leakage Current		50		μA	Max	V <sub>OUT</sub> = V <sub>CC</sub> (A <sub>n</sub> , B <sub>n</sub> )	
I <sub>ZZ</sub>	Bus Drainage Test		100		μA	0.0	V <sub>OUT</sub> = 5.5V (A <sub>n</sub> , B <sub>n</sub> ); All Others GND	
I <sub>CCH</sub>	Power Supply Current		50		μA	Max	All Outputs HIGH	
I <sub>CCL</sub>	Power Supply Current		30		mA	Max	All Outputs LOW	
I <sub>CCZ</sub>	Power Supply Current		50		μA	Max	$\overline{OE}$ = V <sub>CC</sub> , T/ $\overline{R}$ = GND or V <sub>CC</sub> ; All Other GND or V <sub>CC</sub>	
I <sub>CC</sub> T	Additional Outputs Enabled I <sub>CC</sub> /Input	Outputs TRI-STATE	2.5		mA	Max	V <sub>I</sub> = V <sub>CC</sub> - 2.1V $\overline{OE}$ , T/ $\overline{R}$ V <sub>I</sub> = V <sub>CC</sub> - 2.1V Data Input V <sub>I</sub> = V <sub>CC</sub> - 2.1V All Others at V <sub>CC</sub> or GND.	
		Outputs TRI-STATE	2.5		mA			
		Outputs TRI-STATE	50		μA			

## DC Electrical Characteristics (Continued)

Symbol	Parameter	ABT245			Units	V <sub>CC</sub>	Conditions
		Min	Typ	Max			
I <sub>CCD</sub>	Dynamic I <sub>CC</sub> No Load  (Note 3)			0.1	mA/ MHz	Max	Outputs Open  $\overline{OE} = \text{GND}$ , $T/\overline{R} = \text{GND}$ or V <sub>CC</sub> One Bit Toggling, 50% Duty Cycle (Note 4)

**Note 3:** Guaranteed but not tested.

**Note 4:** For 8 bits toggling, I<sub>CCD</sub> < 0.8 mA/MHz.

## DC Electrical Characteristics

Symbol	Parameter	Min	Max	Units	V <sub>CC</sub>	Conditions C <sub>L</sub> = 50 pF, R <sub>L</sub> = 500Ω
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>		1.1	V	5.0	T <sub>A</sub> = 25°C (Note 5)
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>		-0.45	V	5.0	T <sub>A</sub> = 25°C (Note 5)

**Note 5:** Max number of outputs defined as (n). n – 1 data inputs are driven 0V to 3V. One output at LOW.

## AC Electrical Characteristics

Symbol	Parameter	54ABT		Units
		T <sub>A</sub> = -55°C to +125°C V <sub>CC</sub> = 4.5V–5.5V C <sub>L</sub> = 50 pF		
		Min	Max	
t <sub>PLH</sub>	Propagation Delay	1.0	4.8	ns
t <sub>PHL</sub>	Data to Outputs	1.0	4.8	
t <sub>PZH</sub>	Output Enable	1.0	6.7	ns
t <sub>PZL</sub>	Time	2.0	7.5	
t <sub>PHZ</sub>	Output Disable	1.7	7.4	ns
t <sub>PLZ</sub>	Time	1.7	6.5	

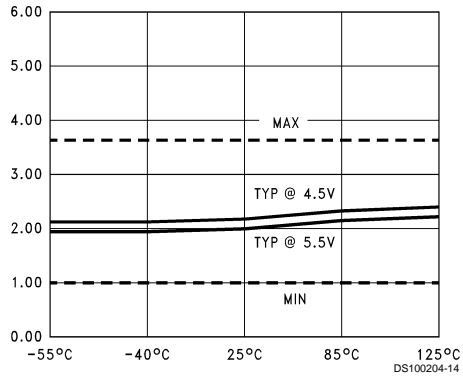
## Capacitance

Symbol	Parameter	Typ	Units	Conditions T <sub>A</sub> = 25°C
C <sub>IN</sub>	Input Capacitance	5.0	pF	V <sub>CC</sub> = 0V ( $\overline{OE}$ , T/ $\overline{R}$ )
C <sub>I/O</sub> (Note 6)	I/O Capacitance	11.0	pF	V <sub>CC</sub> = 5.0V (A <sub>n</sub> , B <sub>n</sub> )

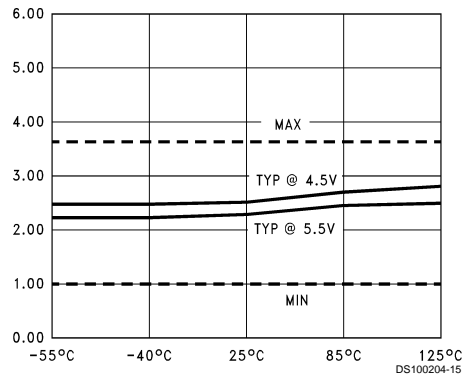
**Note 6:** C<sub>I/O</sub> is measured at frequency f = 1 MHz, per MIL-STD-883B, Method 3012.

## Capacitance (Continued)

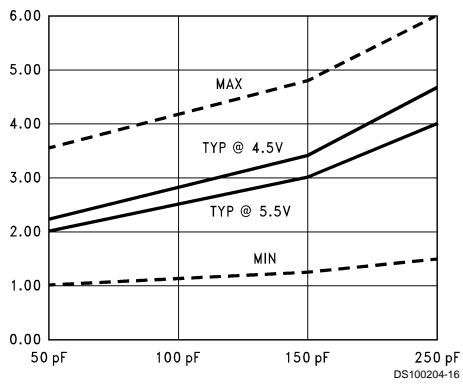
**$t_{PLH}$  vs Temperature ( $T_A$ )**  
 $C_L = 50$  pF, 1 Output Switching



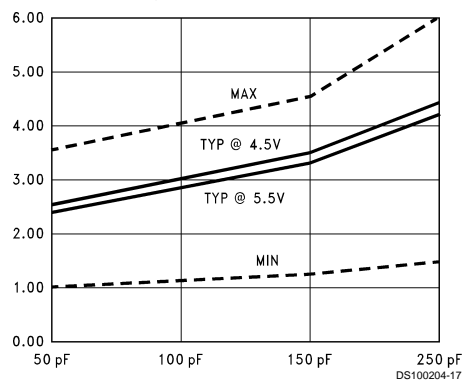
**$t_{PHL}$  vs Temperature ( $T_A$ )**  
 $C_L = 50$  pF, 1 Output Switching



**$t_{PLH}$  vs Load Capacitance**  
 1 Output Switching,  $T_A = 25^\circ\text{C}$

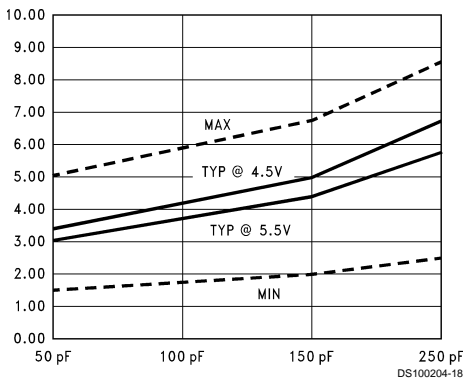


**$t_{PHL}$  vs Load Capacitance**  
 1 Output Switching,  $T_A = 25^\circ\text{C}$

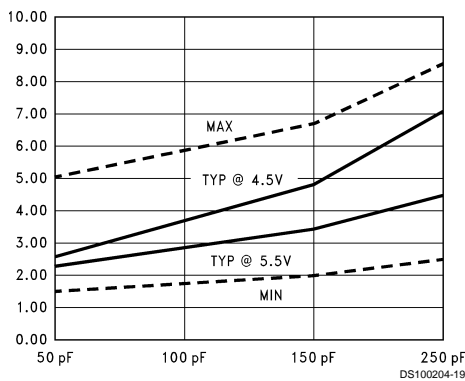


Dashed lines represent design characteristics; for specified guarantees, refer to AC Characteristics Table.

**$t_{PLH}$  vs Load Capacitance**  
 8 Outputs Switching,  $T_A = -40^\circ\text{C}$  to  $+85^\circ\text{C}$

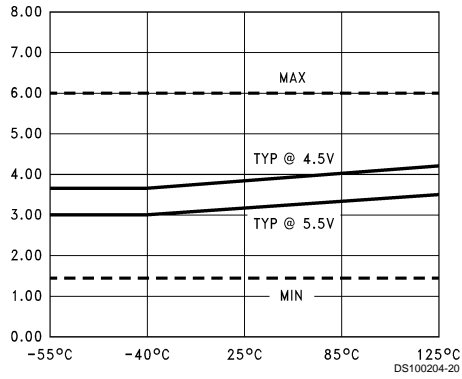


**$t_{PHL}$  vs Load Capacitance**  
 8 Outputs Switching,  $T_A = 25^\circ\text{C}$

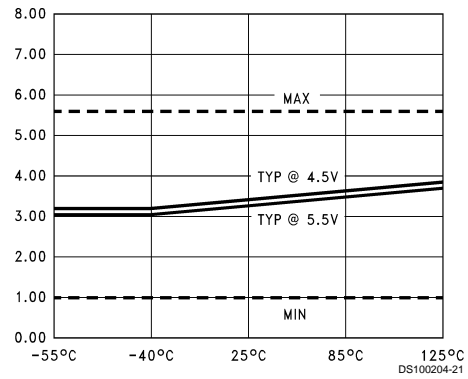


## Capacitance (Continued)

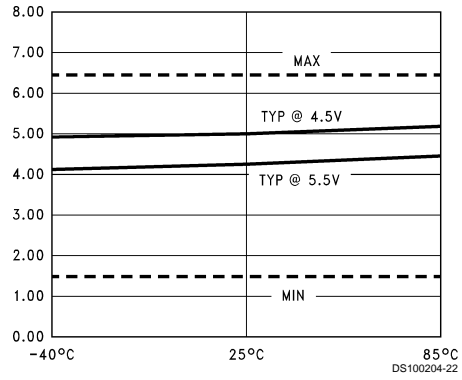
**$t_{PZL}$  vs Temperature ( $T_A$ )**  
 **$C_L = 50$  pF, 1 Output Switching**



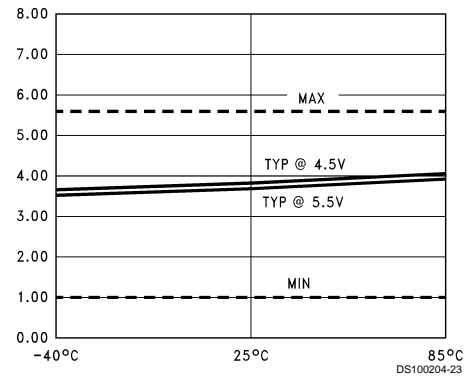
**$t_{PLZ}$  vs Temperature ( $T_A$ )**  
 **$C_L = 50$  pF, 1 Output Switching**



**$t_{PZL}$  vs Temperature ( $T_A$ )**  
 **$C_L = 50$  pF, 8 Outputs Switching**

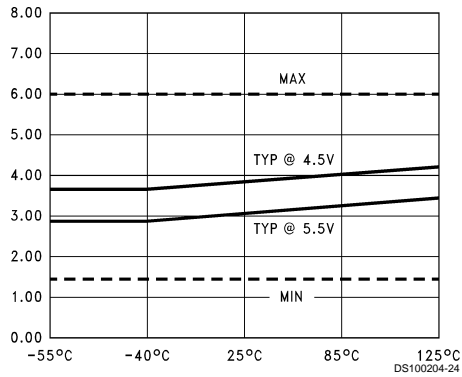


**$t_{PLZ}$  vs Temperature ( $T_A$ )**  
 **$C_L = 50$  pF, 8 Outputs Switching**

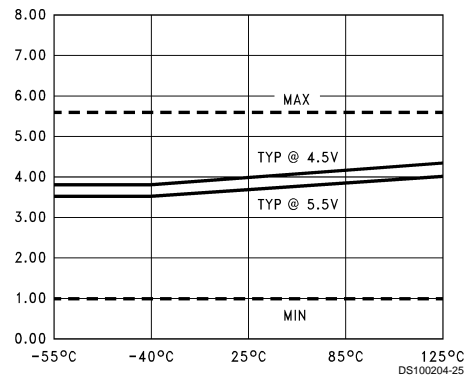


Dashed lines represent design characteristics; for specified guarantees, refer to AC Characteristics Table.

**$t_{PZH}$  vs Temperature ( $T_A$ )**  
 **$C_L = 50$  pF, 1 Output Switching**

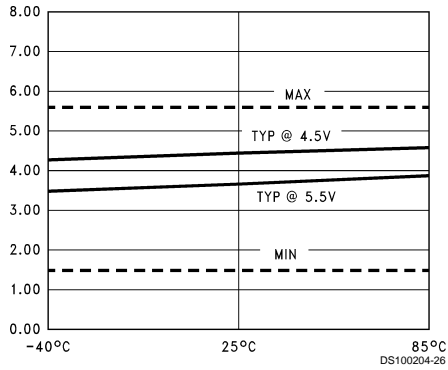


**$t_{PHZ}$  vs Temperature ( $T_A$ )**  
 **$C_L = 50$  pF, 1 Output Switching**

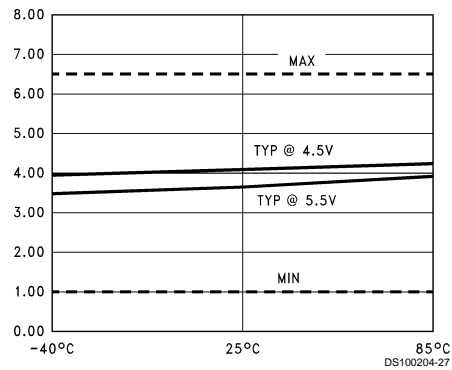


## Capacitance (Continued)

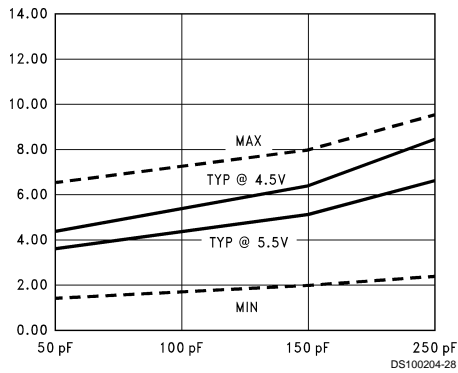
**$t_{PZH}$  vs Temperature ( $T_A$ )**  
 $C_L = 50$  pF, 8 Outputs Switching



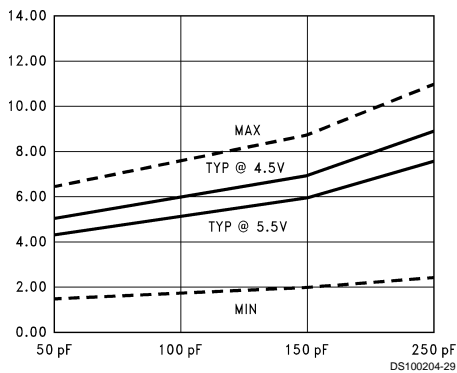
**$t_{PHZ}$  vs Temperature ( $T_A$ )**  
 $C_L = 50$  pF, 8 Outputs Switching



**$t_{PZH}$  vs Load Capacitance**  
 8 Outputs Switching,  $T_A = 25^\circ\text{C}$

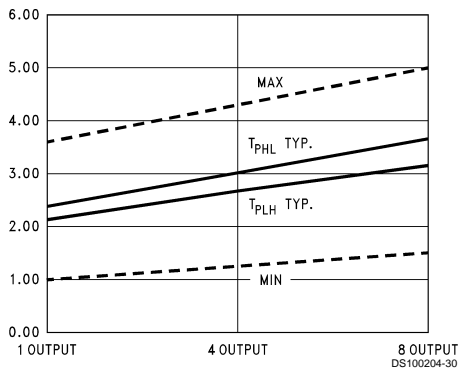


**$t_{PZL}$  vs Load Capacitance**  
 8 Outputs Switching,  $T_A = 25^\circ\text{C}$

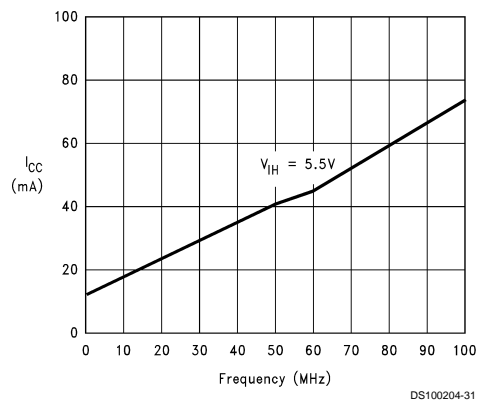


Dashed lines represent design characteristics; for specified guarantees, refer to AC Characteristics Table.

**$t_{PLH}$  and  $t_{PHL}$  vs Number Outputs Switching**  
 $V_{CC} = 5.0\text{V}$ ,  $T_A = 25^\circ\text{C}$ ,  $C_L = 50$  pF

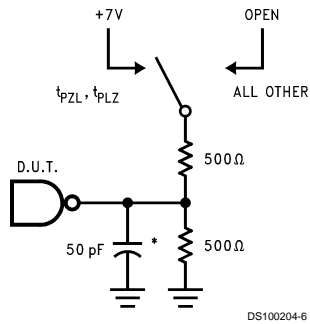


**$I_{CC}$  vs Frequency, Average,  $T_A = 25^\circ\text{C}$ ,**  
 All Outputs Unloaded/Unterminated



Dashed lines represent design characteristics; for specified guarantees, refer to AC Characteristics Table.

## AC Loading



\*Includes jig and probe capacitance

FIGURE 1. Standard AC Test Load

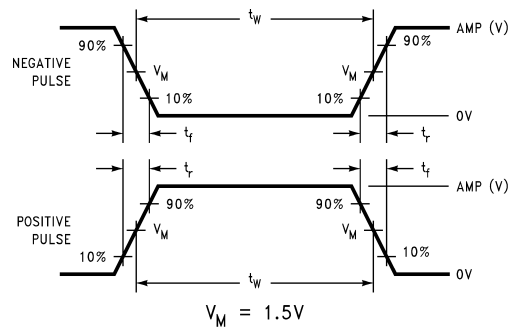


FIGURE 2. Test Input Signal Levels

Amplitude	Rep. Rate	$t_w$	$t_r$	$t_f$
3.0V	1 MHz	500 ns	2.5 ns	2.5 ns

FIGURE 3. Test Input Signal Requirements

## AC Waveforms

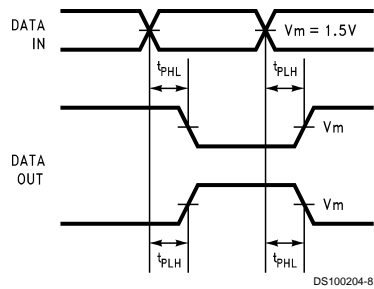


FIGURE 4. Propagation Delay Waveforms for Inverting and Non-Inverting Functions

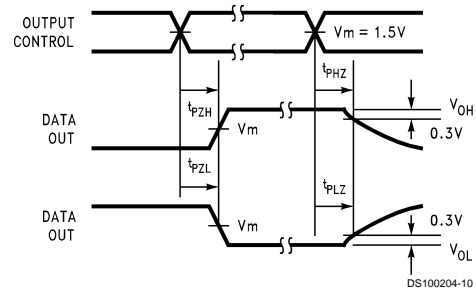
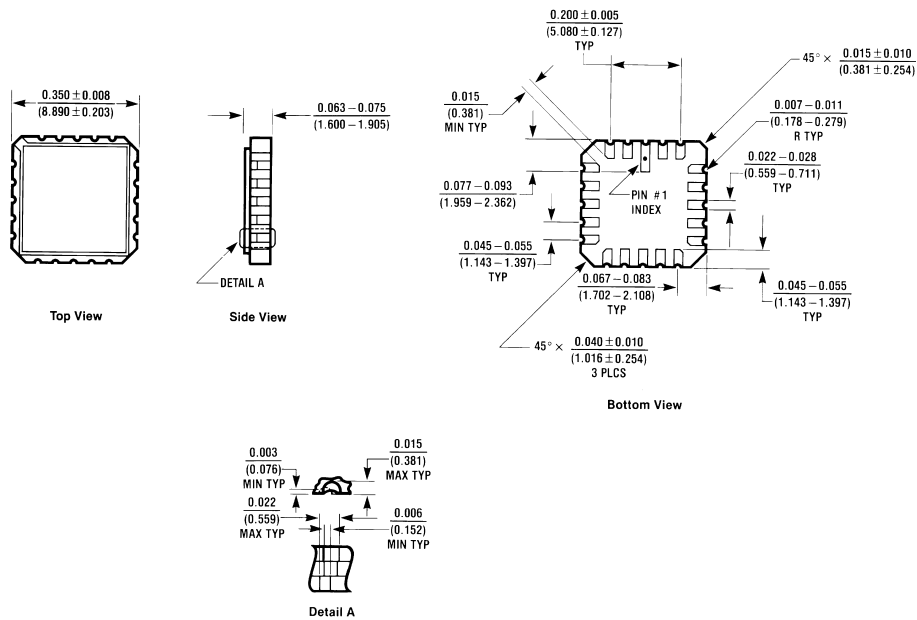


FIGURE 5. TRI-STATE Output HIGH and LOW Enable and Disable Times

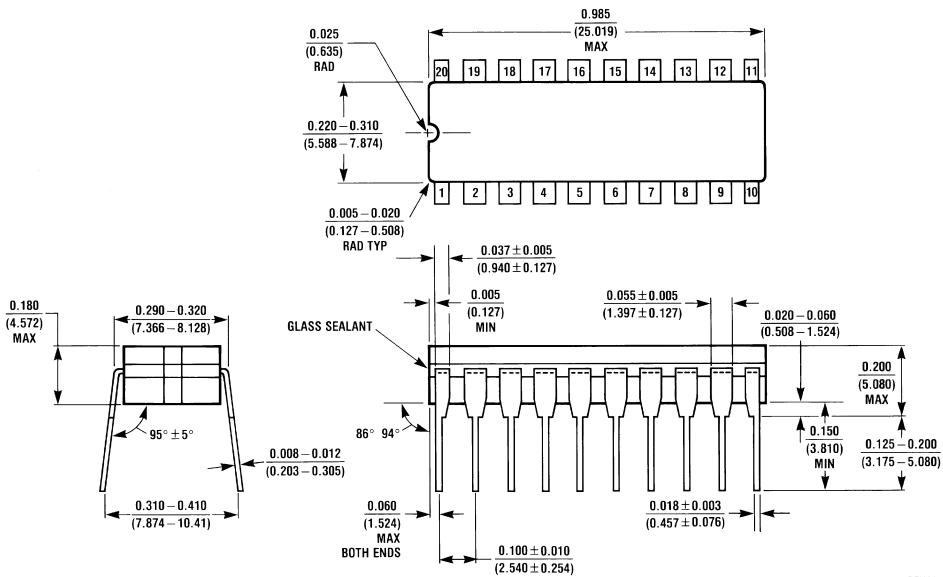


**Physical Dimensions** inches (millimeters) unless otherwise noted



E20A (REV D)

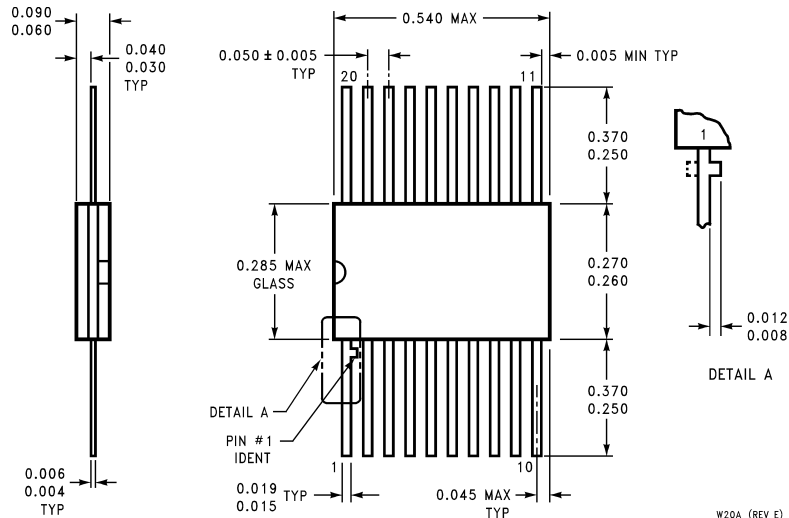
**20-Terminal Ceramic Chip Carrier (L)**  
**NS Package Number E20A**



J20A (REV M)

**20-Lead Ceramic Dual-In-Line Package (D)**  
**NS Package Number J20A**

**Physical Dimensions** inches (millimeters) unless otherwise noted (Continued)



**20-Lead Ceramic Flatpak (F)  
NS Package Number W20A**

W20A (REV E)

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